ON Semiconductor

Is Now

Onsemí

To learn more about onsemi[™], please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI: and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application is the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application, Buyer shall indemnify and hold ons

2-Bit Translating Bus Switch

7WBD3126

The 7WBD3126 is an advanced high-speed low-power 2-bit translating bus switch in ultra-small footprints.

Features

- High Speed: $t_{PD} = 0.25 \text{ ns} (Max) @ V_{CC} = 4.5 \text{ V}$
- 3 Ω Switch Connection Between 2 Ports
- Power Down Protection Provided on Inputs
- Zero Bounce
- TTL-Compatible Control Inputs
- Ultra-Small Pb-Free Packages
- These are Pb-Free Devices



ON Semiconductor®

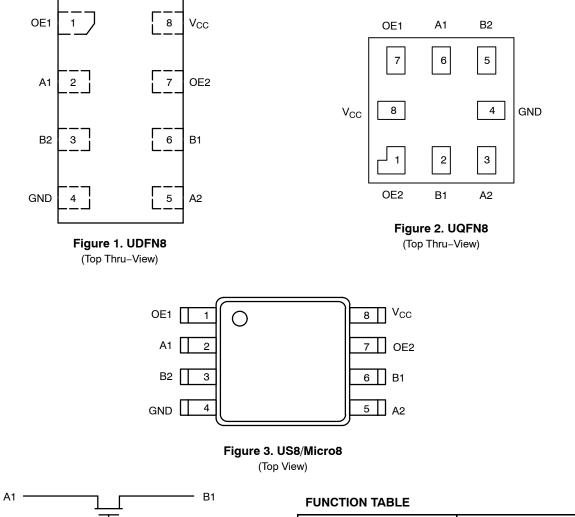
www.onsemi.com

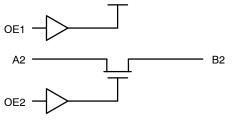
| | | MARKING DIAGRAMS |
|---------------------------------------|---|---|
| 1 | UDFN8 MU SUFFIX CASE 517AJ | AGM o • |
| | UDFN8 1.95 x 1.0 CASE 517CA | 1 • X M |
| | Micro8 DM SUFFIX CASE 846A | 8 A A A D125 AYW- O - 1 1 1 1 1 |
| | UQFN8 MU SUFFIX CASE 523AN | 1 ○ AF M*■ ■ |
| CURN | US8 US SUFFIX CASE 493 | AD ALYW Commercial |
| AG, X, D125, M A L Y W | = Date (= Assen = Lot Co = Year (= Week | nbly Location ode Code |
| (Note: Microd | ot may be in either lo | cation) |

(Note: *Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.







| Input OEn | Function |
|-----------|------------|
| L | Disconnect |
| Н | Bn = An |

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|------------------|---|--|---------------------------|------|
| V _{CC} | DC Supply Voltage | | -0.5 to +7.0 | V |
| V _{IN} | Control Pin Input Voltage | | –0.5 to +7.0 | V |
| V _{I/O} | Switch Input / Output Voltage | | -0.5 to +7.0 | V |
| I _{IK} | Control Pin DC Input Diode Current | V _{IN} < GND | -50 | mA |
| I _{OK} | Switch I/O Port DC Diode Current | V _{I/O} < GND | -50 | mA |
| Ι _Ο | ON-State Switch Current | | ±128 | mA |
| | Continuous Current Through V_{CC} or GND | | ±150 | mA |
| I _{CC} | DC Supply Current Per Supply Pin | | ±150 | mA |
| I _{GND} | DC Ground Current per Ground Pin | | ±150 | mA |
| T _{STG} | Storage Temperature Range | | –65 to +150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds | | 260 | °C |
| TJ | Junction Temperature Under Bias | | 150 | °C |
| θ_{JA} | Thermal Resistance | US8 (Note 1) UDFN8 UQFN8 Micro8 | 251 111 208 392 | °C/W |
| P _D | Power Dissipation in Still Air at 85°C | US8 UDFN8 UQFN8 Micro8 | 498 1127 601 319 | mW |
| MSL | Moisture Sensitivity | | Level 1 | |
| F _R | Flammability Rating Oxygen Index: 28 to 34 | | UL 94 V-0 @ 0.125 in | |
| V _{ESD} | ESD Withstand Voltage Human Body Mode (Note 2) Machine Model (Note 3) Charged Device Model (Note 4) | | > 2000 > 200 N/A | V |
| ILATCHUP | Latchup Performance Above V _{CC} and Below GN | D at 125°C (Note 5) | ±200 | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

2. Tested to EIA / JESD22-A114-A.

Tested to EIA / JESD22-A115-A.
 Tested to JESD22-C101-A.

5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | Min | Max | Unit |
|------------------|--|--|--------|---------|------|
| V _{CC} | Positive DC Supply Voltage | | 4.0 | 5.5 | V |
| V _{IN} | Control Pin Input Voltage | | 0 | 5.5 | V |
| V _{I/O} | Switch Input / Output Voltage | | 0 | 5.5 | V |
| T _A | Operating Free-Air Temperature | | -55 | +125 | °C |
| Δt/ΔV | Input Transition Rise or Fall Rate Control Input Switch I/O | | 0 0 | 5 DC | nS/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

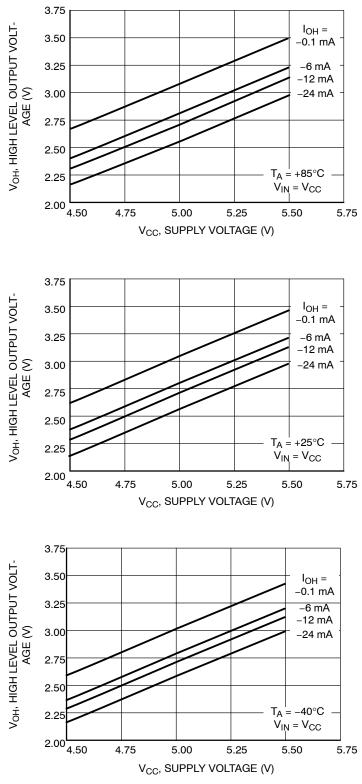
| | | | | | T _A = 25°C | | T _A = −55°C to +125°C | | |
|------------------|---|---|------------------------|-----|-----------------------|--------------|-------------------------------------|--------------|----------|
| Symbol | Parameter | Conditions | V _{CC} (V) | Min | Тур | Max | Min | Max | Unit |
| V _{IK} | Clamp Diode Voltage | I _{I/O} = -18 mA | 4.5 | | | -1.2 | | -1.2 | V |
| V _{IH} | High-Level Input Voltage (Control) | | 4.0 to 5.5 | 2.0 | | | 2.0 | | V |
| V _{IL} | Low-Level Input Voltage (Control) | | 4.0 to 5.5 | | | 0.8 | | 0.8 | V |
| V _{OH} | Output Voltage High | See Figure 5 | | | | | | | |
| I _{IN} | Input Leakage Current | $0 \le V_{IN} \le 5.5 V$ | 5.5 | | | ±0.1 | | ±1.0 | μA |
| I _{OFF} | Power Off Leakage Current | V _{I/O} = 0 to 5.5 V | 0 | | | ±0.1 | | ±1.0 | μΑ |
| Icc | Quiescent Supply Current | $\label{eq:loss} \begin{array}{l} I_O = 0, \\ V_{IN} = V_{CC} \text{ or } 0 \text{ V} \\ OE1 = OE2 = V_{CC} \\ OE1 = OE2 = GND \end{array}$ | 5.5 | | | ±1.0 ±0.1 | | ±1.0 ±1.0 | mA μA |
| ΔI_{CC} | Increase in Supply Current (Control Pin) | One input at 3.4 V; Other inputs at V_{CC} or GND | 5.5 | | | | | 2.5 | mA |
| R _{ON} | Switch ON Resistance | $V_{I/O} = 0,$ $I_{I/O} = 64 \text{ mA}$ $I_{I/O} = 30 \text{ mA}$ | 4.5 | | 3 3 | 7 7 | | 7 7 | Ω |
| | | V _{I/O} = 2.4, I _{I/O} = 15 mA | | | 15 | 50 | | 50 | |
| | | V _{I/O} = 2.4, I _{I/O} = 15 mA | 4.0 | | 50 | 70 | | 70 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

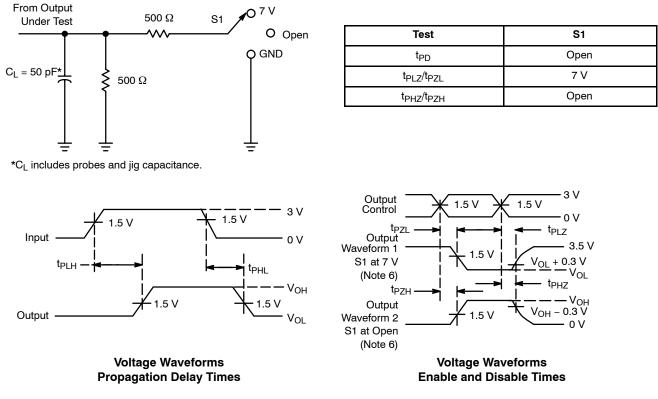
| | | | V _{CC} T _A = 25 °C | | T _A = -55°C to +125°C | | | | |
|----------------------|----------------------------------|----------------------------|--|-----|-------------------------------------|------|-----|------|------|
| Symbol | Parameter | Test Condition | (V) | Min | Тур | Мах | Min | Max | Unit |
| t _{PD} | Propagation Delay, Bus to Bus | See Figure 6 | 4.0 to 5.5 | | | 0.25 | | 0.25 | ns |
| t _{EN} | Output Enable Time | See Figure 6 | 4.5 to 5.5 | 0.8 | 2.5 | 4.2 | 0.8 | 4.2 | ns |
| | | | 4.0 | 0.8 | 3.0 | 4.6 | 0.8 | 4.6 | |
| t _{DIS} | Output Disable Time | | 4.5 to 5.5 | 0.8 | 3.0 | 4.8 | 0.8 | 4.8 | ns |
| | | | 4.0 | 0.8 | 2.9 | 4.4 | 0.8 | 4.4 | |
| C _{IN} | Control Input Capacitance | V _{IN} = 5 or 0 V | 5.0 | | 2.5 | | | | pF |
| C _{IO(ON)} | Switch On Capacitance | Switch ON | 5.0 | | 10 | | | | pF |
| C _{IO(OFF)} | Switch Off Capacitance | Switch OFF | 5.0 | | 5 | | | | pF |

TYPICAL DC CHARACTERISTICS





AC LOADING AND WAVEFORMS



Parameter Measurement Information

6. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control

7. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns. 8. The outputs are measured one at a time, with one transition per measurement.

9. t_{PLZ} and t_{PHZ} are the same as t_{DIS}.

10. t_{PZL} and t_{PZH} are the same as t_{EN} . 11. t_{PHL} and t_{PLH} are the same as t_{PD} .

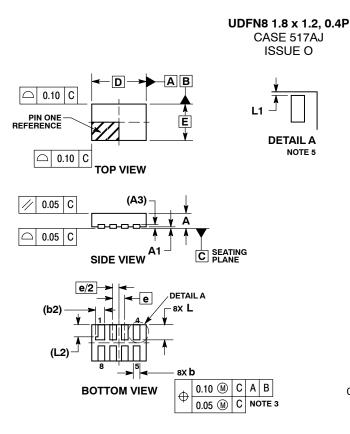


ORDERING INFORMATION

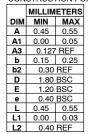
| Device | Package | Shipping [†] |
|----------------|--------------------------------------|-----------------------|
| 7WBD3126USG | US8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3126MUTAG | UDFN8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3126AMUTCG | UQFN8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3126DMR2G | Micro8 (Pb-Free) | 4000 / Tape & Reel |
| 7WBD3126DMUTCG | UDFN8, 1.95 x 1.0, 0.5P (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

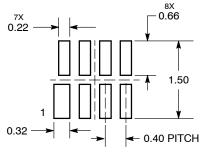
PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
 4. MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM
- ALONG EDGE OF PACKAGE. FLASF-NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS. 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.



MOUNTING FOOTPRINT* SOLDERMASK DEFINED

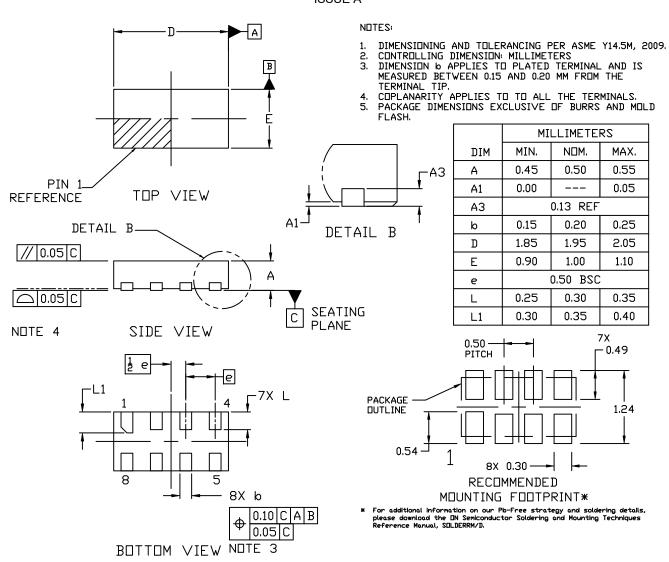


DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

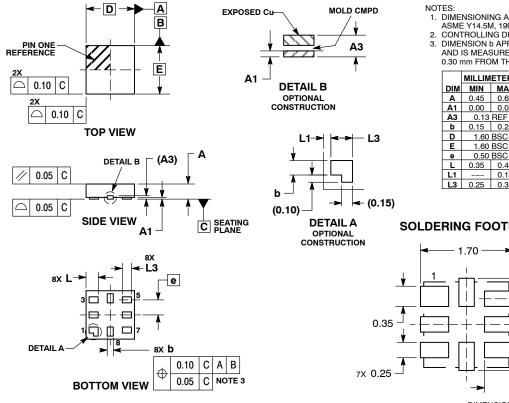
PACKAGE DIMENSIONS

UDFN8 1.95x1.0, 0.5P CASE 517CA ISSUE A



PACKAGE DIMENSIONS

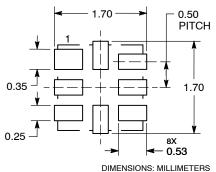
UQFN8, 1.6x1.6, 0.5P CASE 523AN ISSUE O



DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

| | MILLIMETERS | | | | |
|-----|-------------|----------|--|--|--|
| DIM | MIN | MAX | | | |
| Α | 0.45 | 0.60 | | | |
| A1 | 0.00 | 0.05 | | | |
| A3 | 0.13 | REF | | | |
| b | 0.15 | 0.25 | | | |
| D | 1.60 | 1.60 BSC | | | |
| Е | 1.60 | BSC | | | |
| е | 0.50 | BSC | | | |
| L | 0.35 | 0.45 | | | |
| L1 | 0.15 | | | | |
| L3 | 0.25 | 0.35 | | | |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

US8 **CASE 493** ISSUE D

INCHES

MIN MAX

0.024 0.035

0.008 0.014

0.020 BSC

0.016 REF

0.004 0.007

0.009 0.013

0.005 BSC

0.083

0.094

0.010

0.004

0.128

6

10 °

0.013

0.075

0.087

0.007

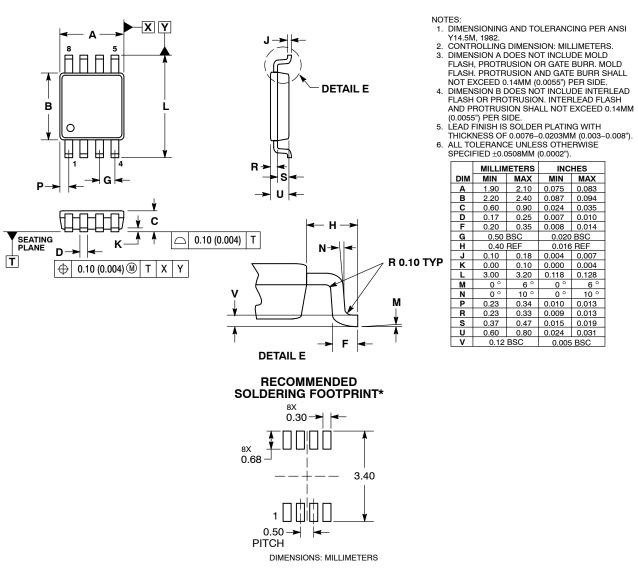
0.000

0.118

0

0.010

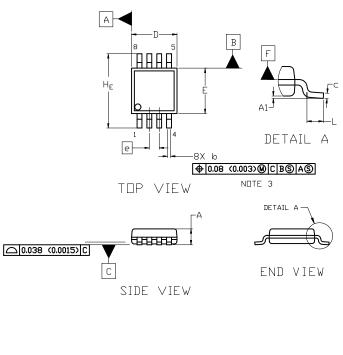
0 °



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

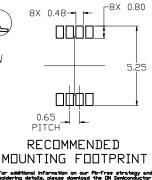
PACKAGE DIMENSIONS

Micro8 CASE 846A ISSUE K



NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- 5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- 6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



| DIM | MI | LLIMETE | RS | | | |
|-----|------|----------|------|--|--|--|
| DIM | MIN. | NDM. | MAX. | | | |
| A | | | 1.10 | | | |
| A1 | 0.05 | 0.08 | 0.15 | | | |
| b | 0.25 | 0.33 | 0.40 | | | |
| С | 0.13 | 0.18 | 0.23 | | | |
| D | 2.90 | 3.00 | 3.10 | | | |
| E | 2.90 | 3.00 | 3.10 | | | |
| e | l | 0.65 BSC | | | | |
| HE | 4.75 | 4.90 | 5.05 | | | |
| L | 0.40 | 0.55 | 0.70 | | | |

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor asche and application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor hardus spaginst all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semicond

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

٥